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Insight into the structural, electronic and elastic properties of AlnQ₂ (A: K, Rb and Q: S, Se, Te) layered structures from first-principles calculations

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ACCEPTED MANUSCRIPT

Highlights

- Some physical properties of AInQ2 (A: K, Rb and Q: S, Se,Te) are investigated
- The ground states properties compare well with the available published data
- The studied compounds are direct gap semiconductors
- The mechanical properties are investigated for the first time



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